MONDAY, March 27, TUTORIALS 8a.m.-5:00 p.m.

<table>
<tr>
<td>201.
Reliability challenges for ultra-thin oxide
T. Nigam (Cypress Semi)
(8:00-9:30 a.m.)</td>
<td>220.
The role of reliability mechanisms in the architecture and design of embedded RAMs
W.F. Ellis (IBM)
(8:00-9:30 a.m.)</td>
<td>241.
Interconnect dimension and current waveform effects on electromigration performance
Y.-J. Park (TI)
(8:00-9:30 a.m.)</td>
<td>250.
Reliability challenges in integrated high voltage devices
P. Moens (AMI)
(8:00-9:30 a.m.)</td>
</tr>
<tr>
<td>202.
Gate oxide breakdown in FET devices and circuits
B. Kaczer (IMEC)
(10:00-11:30 a.m.)</td>
<td>230.
IC testing for reliability
K.M. Butler (TI)
(10:00-11:30 a.m.)</td>
<td>242.
Mechanical aspects – interconnects
Z. Suo (Harvard)
(10:00-11:30 a.m.)</td>
<td rowspan="2">260.
Reinventing CMOS (to stay on Moore's law)
T. Dellin (Quick Start Micro Training)
(10:00-11:30 a.m.
And
(1:00-2:30 p.m.)</td>
</tr>
<tr>
<td>210.
Electrical characterization of high-k gate dielectrics
M. Takayanagi (Toshiba)
1:00-2:30 p.m.)</td>
<td></td>
<td>243.
Cu microstructure impact on reliability
J. Koike (Tohoku Univ)
(1:00-2:30 p.m.)</td>
</tr>
</table>